

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
28 July 2005 (28.07.2005)

PCT

(10) International Publication Number
WO 2005/069401 A1

(51) International Patent Classification⁷: H01L 51/20

(21) International Application Number:
PCT/CIB2005/000132

(22) International Filing Date: 17 January 2005 (17.01.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
0400997.3 16 January 2004 (16.01.2004) GB

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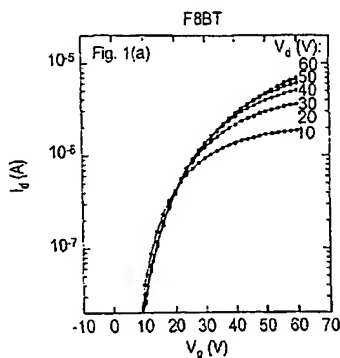
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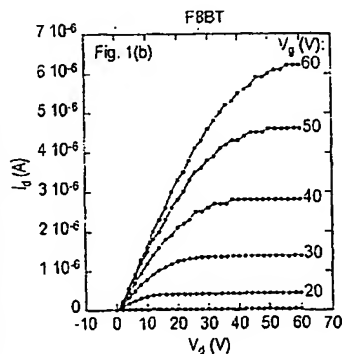
(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, PA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,

[Continued on next page]

(54) Title: N-CHANNEL TRANSISTOR



(57) Abstract: An n-channel or ambipolar field-effect transistor including an organic semiconductive layer having an electron affinity EA_{semicond} ; and an organic gate dielectric layer forming an interface with the semiconductive layer; characterised in that the bulk concentration of trapping groups in the gate dielectric layer is less than 10^{18}cm^{-3} , where a trapping group is a group having (i) an electron affinity EA_x greater than or equal to EA_{semicond} and/or (ii) a reactive electron affinity EA_{rxn} greater than or equal to $(EA_{\text{semicond}} - 2\text{eV})$.



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TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

- with international search report

- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

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